MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PIFD

MMST5401

Product specification





FEATURES

- Complementary to MMST5551
- Small Surface Mount Package
- Ideal for Medium Power Amplification and Switching

Reference News

PACKAGE OUTLINE		MARKING
3	1. BASE 2. EMITTER 3. COLLECTOR	K4M
SOT-323		

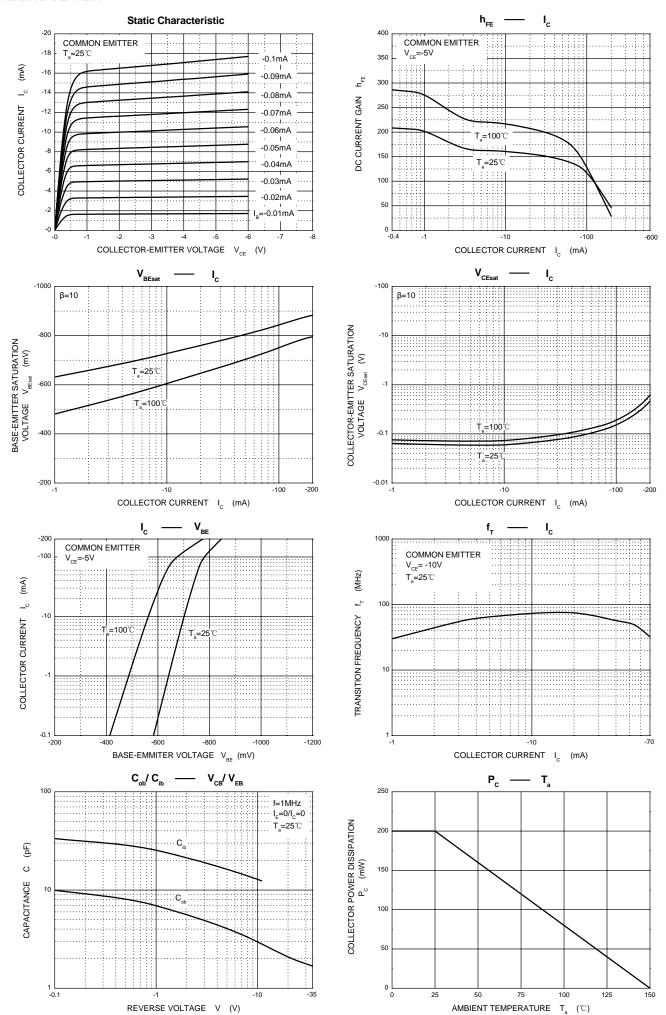
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-160	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current	-600	mA
Pc	Collector Power Dissipation	200	mW
Roja	Thermal Resistance From Junction To Ambient	625	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55 ~ +150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

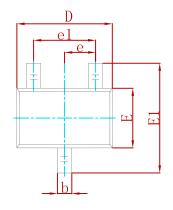
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	lc=-100μA, I _E =0	-160			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	Ісво	V _{CB} =-120V, I _E =0			-50	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-3V, I _C =0			-50	nA
DC current gain	hFE	V _{CE} =-5V, I _C =-1mA	50			
		V _{CE} =-5V, I _C =-10mA	100		300	
		V _{CE} =-5V, I _C =-50mA	50			
0-11	V	I _C =-50mA, I _B =-5mA			-0.5	V
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10mA, I _B =-1mA			-0.2	V
Dana amilitar actionation valtare	V _{BE(sat)}	I _C =-50mA, I _B =-5mA			-1	V
Base-emitter saturation voltage		lc=-10mA, l _B =-1mA			-1	V
Transition frequency	f⊤	V _{CE} =-10V,I _C =-10mA , f=100MHz	100			MHz
Collector output capacitance	Cob	V _{CB} =-10V, I _E =0, f=1MHz			6	pF

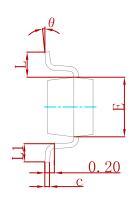


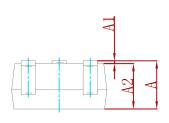




PACKAGEMECHANICALDATA

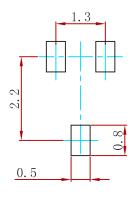






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650 TYP		0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021	I REF	
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMST5401	SOT-323	3000



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